

Silicon NPN Power Transistors

BU326 BU326A

DESCRIPTION

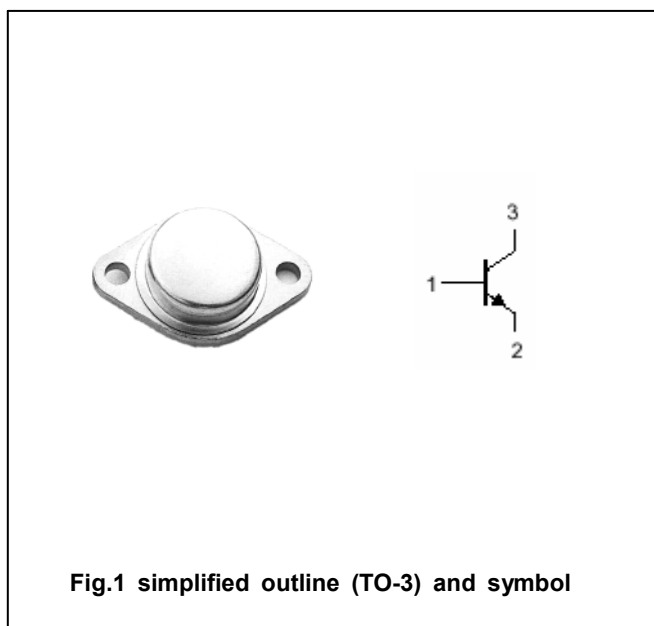
- With TO-3 package
- High voltage;high speed
- Low collector saturation voltage.

APPLICATIONS

- Intended for operating in CTV receiver's chopper supplies.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings ($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BU326	Open emitter	800	V
		BU326A		900	
V_{CEO}	Collector-emitter voltage	BU326	Open base	375	V
		BU326A		400	
V_{EBO}	Emitter-base voltage		Open collector	10	V
I_C	Collector current			6	A
I_{CM}	Collector current-peak			8	A
I_B	Base current			3	A
P_T	Total power dissipation		$T_c=25$	75	W
T_j	Junction temperature			-65~200	
T_{stg}	Storage temperature			-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	2.33	/W

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	BU326	$I_C=0.1A; I_B=0$	375			V
		BU326A		400			
$V_{CEsat-1}$	Collector-emitter saturation voltage		$I_C=2.5A; I_B=0.5A$			1.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage		$I_C=4A; I_B=1.25A$			3.0	V
$V_{BEsat-1}$	Base-emitter saturation voltage		$I_C=2.5A; I_B=0.5A$			1.4	V
$V_{BEsat-2}$	Base-emitter saturation voltage		$I_C=4A; I_B=1.25A$			1.6	V
I_{CES}	Collector cut-off current	BU326	$V_{CE}=800V; V_{BE}=0$			1	mA
		BU326A	$V_{CE}=900V; V_{BE}=0$				
I_{EBO}	Emitter cut-off current		$V_{EB}=10V; I_C=0$			10	mA
h_{FE}	DC current gain		$I_C=1A; V_{CE}=5V$		25		
f_T	Transition frequency		$I_C=0.2A; V_{CE}=10V; f=1MHz$	4.0			MHz

Switching times

t_{on}	Turn-on time	$I_C=2.5A; I_{B1}=0.5A; I_{B2}=-1A; V_{CC}=250V;$			0.5	μs
t_s	Storage time				3.5	μs
t_f	Fall time				0.5	μs

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PACKAGE OUTLINE

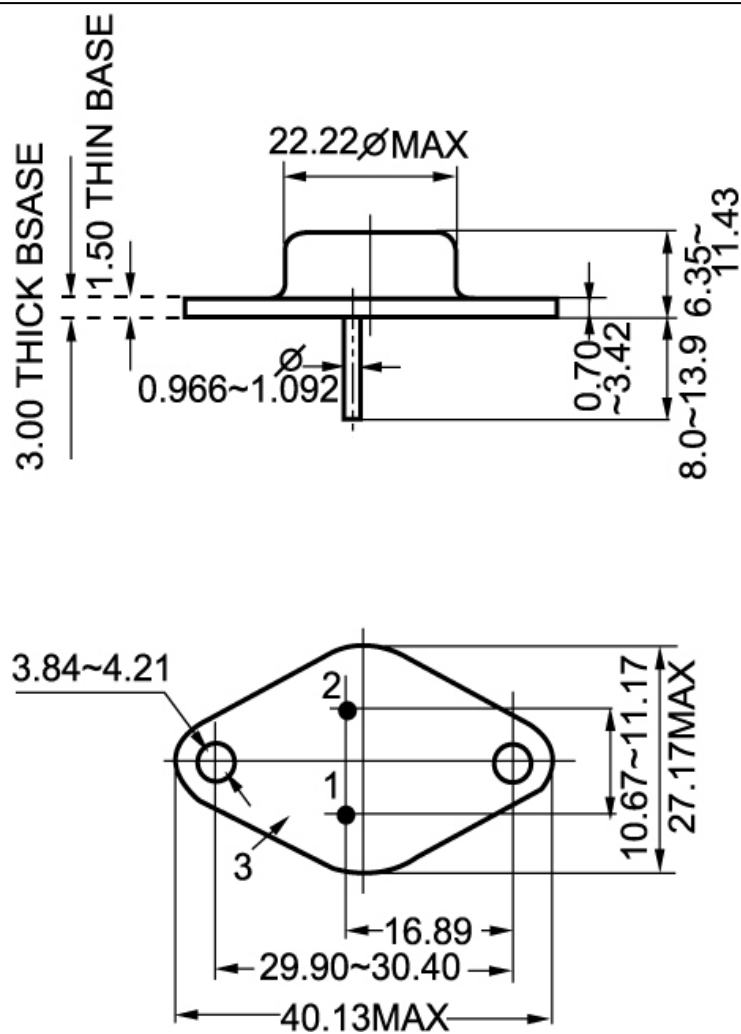


Fig.2 Outline dimensions